Record Nr. UNINA9910831087203321 Amorphous oxide semiconductors: IGZO and related materials for **Titolo** display and memory // Hideo Hosono and Hideya Kumomi, editors Pubbl/distr/stampa Hoboken, NJ:,: John Wiley & Sons, Inc.,, [2022] ©2022 **ISBN** 1-119-71561-X 1-119-71564-4 1-119-71565-2 Descrizione fisica 1 online resource (643 pages) Collana Wiley Series in Display Technology Disciplina 537.622 Soggetti Indium gallium zinc oxide Thin film transistors Amorphous semiconductors Lingua di pubblicazione Inglese **Formato** Materiale a stampa Livello bibliografico Monografia Nota di bibliografia Includes bibliographical references and index. Sommario/riassunto Comprehensive explorations of the electronic structure of amorphous oxide semiconductors, structural randomness, doping limits, and defects. In-depth examinations of thin film transistors (TFTs), including the trade-off relationship between mobility and reliability in oxide. TFTs Perfect for practicing scientists, engineers, and device technologists working with transparent semiconductor systems, Amorphous Oxide Semiconductors: Materials and Device Applications will also earn a place in the libraries of students studying oxides and other non-classical and innovative semiconductor devices"--